



# 《风光欣》技术资料

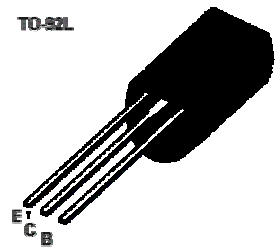
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## 2SD468

### NPN EPITAXIAL SILICON TRANSISTOR

#### ABSOLUTE MAXIMUM RATINGS(Ta=25 )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	25	V
Collector-Emitter Voltage	V <sub>CEO</sub>	20	V
Emitter -Base Voltage	V <sub>EBO</sub>	5	V
Collector Current (DC)	I <sub>c</sub>	1	A
Collector Dissipation (Tc=25 )	P <sub>c</sub>	0.9	W
Junction Temperature	T <sub>J</sub>	150	
Storage Temperature	T <sub>STG</sub>	-55 ~150	



#### ELECTRICAL CHARACTERISTICS(Ta=25 )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 20V,I <sub>E</sub> =0			1	μ A
Emitter-Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> = 3V,I <sub>c</sub> =0			1	μ A
*DC Current Gain	H <sub>fe</sub>	V <sub>CE</sub> = 2V,I <sub>c</sub> = 0.5A	85		300	
*Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> = 0.8A,I <sub>B</sub> = 0.08A		0.2	0.5	V
Current Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> = 2V,I <sub>E</sub> =0.5A		190		MHZ
Output Capacitance	C <sub>OB</sub>	V <sub>CB</sub> = 10V,I <sub>E</sub> =0,f=1MHZ		22		pF

\*Pulse Test

#### HFE CLASSIFICATION

Classification	B	C
HFE	85-160	160-300